

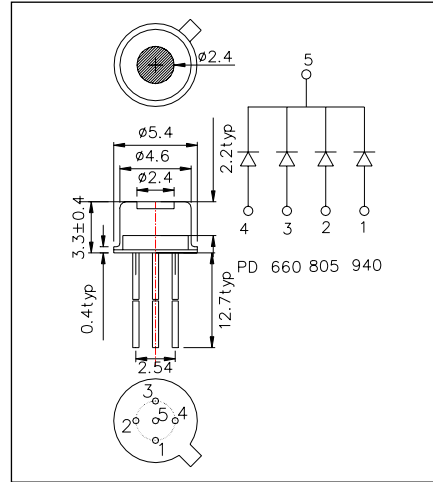
L660/805/940/PD010-35B52
Multi-Wavelength LED

This product consists of AlGaAs(660,805nm), GaAs(940nm) LED and Si-PD mounted on TO-18 stem Hermetical sealed with flat glass lens. It is designed to monitor reflected light through detector for controlling its own output power.

<Specifications>

1. Product Name: Multi-Wavelength LED Lamp
2. Type Number: L660/805/940/PD010-35B52
3. Chip:
 - Chip material: AlGaAs, GaAs and Si-PIN-PD
 - Peak Wavelength: 660,805,940nm
4. Package:
 - Stem: TO-18, 5pins type
 - Lens: Φ2.4mm Flat Glass

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]						
Item	Symbol	Maximum Rated Value				Unit
		660	805	940	PD	
Power Dissipation	PD	120	170	140	-	mW
Forward Current	IF	50	100	100	-	mA
Pulse Forward Current	IFP	200	500	1000	-	mA
Reverse Voltage	VR	5			100	V
Operating Temperature	TOPR	-30 ~ +85				°C
Storage Temperature	TSTG	-30 ~ +100				°C
Soldering Temperature*	TSOL	260				°C

* Soldering condition must be completed within 3 seconds at 260°C and it is allowed in the area apart 3mm from the bottom of the lamp.

Electro-Optical Characteristics [Ta=25°C]													
Item	Symbol	Condition	Minimum			Typical			Maximum			Unit	
			660	805	940	660	805	940	660	805	940		PD
Forward Voltage	VF	IF=20mA				1.9	1.5	1.2	2.2	1.7	1.3		V
Reverse Current	IR	VR=5V							10				uA
T. Radiated Power*	PO	IF=20mA				2.9	3.5	2.5					mW
Peak Wavelength	λ P	IF=20mA	650	795	935	660	805	940	670	915	955		nm
Half Width	Δλ	IF=20mA				20	30	45					nm
Reverse Photo Current	IL	VR=10V				50	130	140					uA
Reverse Dark Current	ID	VR=10V										10	nA

* Measured by Photodyne #500

